**Product data sheet** 

## 1. General description

Ultrafast, epitaxial rectifier diode in a SOT428 (DPAK) surface-mountable package.

## 2. Features and benefits

- · Low forward voltage drop
- Fast switching
- · Soft recovery characteristic
- Surface-mountable package
- · High thermal cycling performance
- Low thermal resistance

## 3. Applications

- High-frequency switched-mode power supplies
- Low loss rectification

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_R$	reverse voltage	DC	-	-	200	V
$V_{RRM}$	repetitive peak reverse voltage		-	-	200	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2	-	-	8	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; with reapplied $V_{RRM(Max)}$	-	-	80	A
Static characte	eristics					
$V_{F}$	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	_	0.92	1.05	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	1.1	1.3	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>	-	0.8	0.895	V
Dynamic chara	acteristics					
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/ $\mu$ s; $T_j$ = 25 °C; ramp recovery; Fig. 6; Fig. 7; Fig. 8	-	20	25	ns
		step recovery; when switched from $I_F$ = 0.5 A to $I_R$ = 1 A measured at $I_R$ = 0.25 A	-	15	20	ns

# **5. Pinning information**

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	no connection		K — A
2	K	cathode[1]	(7 B S)	001aaa020
3	А	anode		
mb	К	mounting base; cathode	DPAK (SOT428)	

<sup>[1]</sup> it is not possible to make connection with Pin 2 of the SOT428 package

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
BYW29ED-200	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

## 7. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	200	V
$V_{RWM}$	crest working reverse voltage		-	200	V
$V_R$	reverse voltage	DC	-	200	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2	-	8	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta = 0.5 \; ; t_p = 25 \; \mu s; T_{mb} \le 128 \; ^{\circ}C$	-	16	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; with reapplied $V_{RRM(Max)}$	-	80	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; with reapplied $V_{RRM(Max)}$	-	88	Α
I <sub>RRM</sub>	repetitive peak reverse current	$\delta = 0.001 \; ; t_p = 2 \; \mu s$	-	0.2	Α
I <sub>RSM</sub>	non-repetitive peak reverse current	$t_p = 100 \ \mu s$	-	0.2	Α
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	150	°C
$V_{ESD}$	electrostatic discharge voltage	C = 250 pF; R = 1.5 kΩ; all pins; human body model	-	8	kV

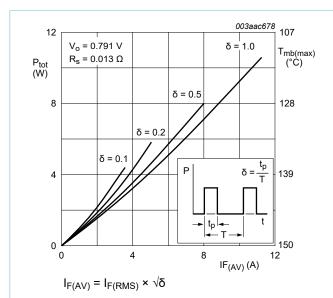


Fig. 1. Total power dissipation and permissible mounting base temperature as a function of average forward current; square waveform; maximum values

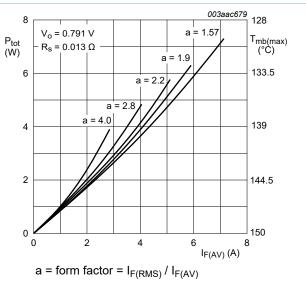


Fig. 2. Total power dissipation and permissible mounting base temperature as a function of average forward current; sinusoidal waveform; maximum values

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## 8. Thermal characteristics

#### **Table 5. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; Fig. 3		-	-	2.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air; Fig. 4	[1]	-	50	-	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin plated and standard footprint

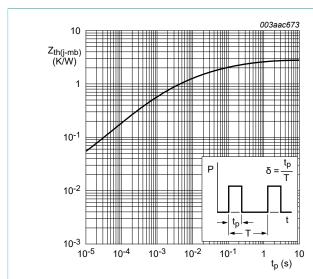


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

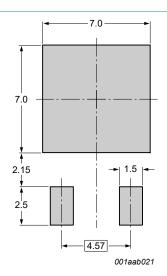


Fig. 4. SOT428: minimum pad sizes for surface-mounting

## 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	0.92	1.05	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	1.1	1.3	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>	-	0.8	0.895	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C	-	2	10	μA
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 100 °C	-	0.2	0.6	mA
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/ $\mu$ s; $T_j$ = 25 °C; ramp recovery; Fig. 6; Fig. 7; Fig. 8	-	20	25	ns
		step recovery; when switched from $I_F$ = 0.5 A to $I_R$ = 1 A measured at $I_R$ = 0.25 A	-	15	20	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 9}}{}$	-	-	1.8	А
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 20 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 10	-	4	11	nC
$V_{FR}$	forward recovery voltage	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 10 A/µs; <u>Fig. 11</u>	-	1	-	V

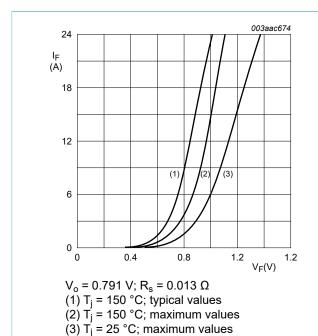


Fig. 5. Forward current as a function of forward voltage

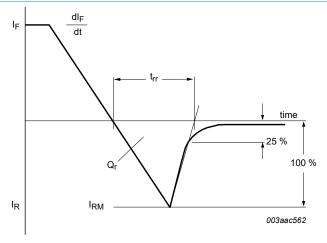


Fig. 6. Reverse recovery definitions; ramp recovery

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### **Ultrafast power diode**

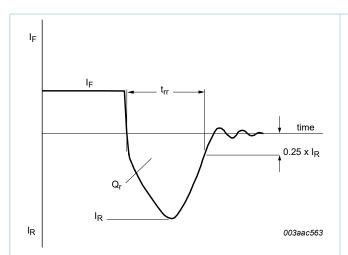


Fig. 7. Reverse recovery definitions; step recovery

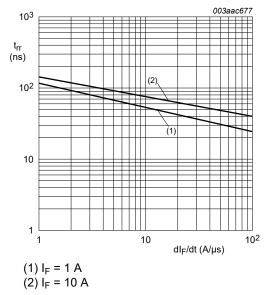


Fig. 8. Reverse recovery time as a function of rate of change of forward current and initial forward current; maximum values

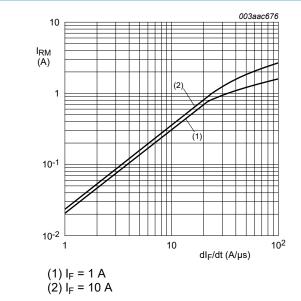


Fig. 9. Peak reverse recovery current as a function of rate of change of forward current and initial forward current; maximum values

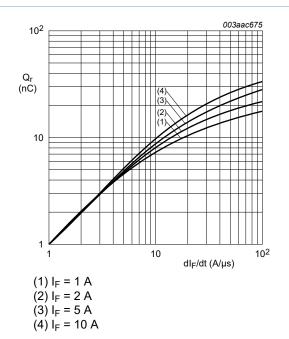
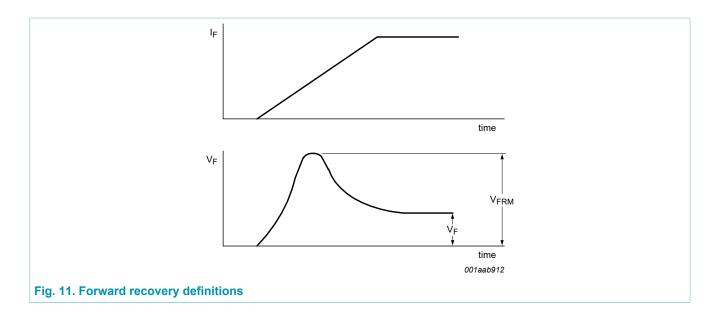


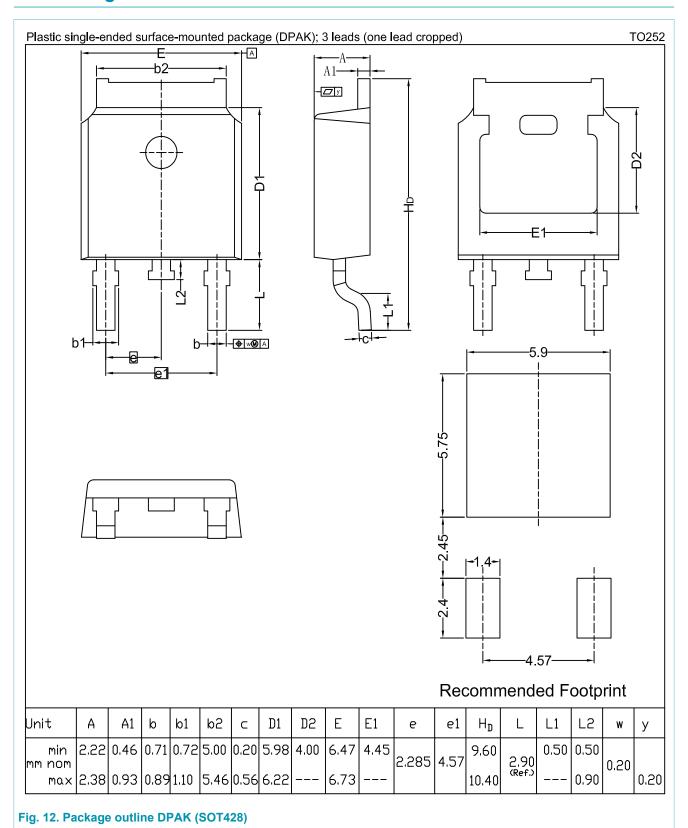
Fig. 10. Recovered charge as a function of rate of change of forward current; maximum values

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## 10. Package outline



## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**BYW29ED-200** 

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Date of release: 26 September 2018

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